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Authors
Liberati, Marco
Scholl, Andreas
Arenholz, Elke
[et al.]

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Planar domain wall in antiferromagnetic/ferromagnetic systems: the Co/NiO case

Marco Liberati$^{1,2}$, Andreas Scholl$^2$, Elke Arenholz$^2$, Hendrik Ohldag$^3$, Luc Thomas$^4$, YunJun Tang$^5$, Ami Berkowitz$^5$, Joachim Stohr$^3$

$^1$Department of Physics, Montana State University, Bozeman, MT 59717, USA
$^2$Lawrence Berkeley National Laboratory, Berkeley, CA 94720, USA
$^3$Stanford Synchrotron Radiation Laboratory, Stanford, CA 94309, USA
$^4$IBM Research Division, Almaden Research Center, San Jose, CA 95120, USA
$^5$Center for Magnetic Recording Research, University of California, San Diego, CA 92093, USA

The exchange bias effect established at the interface between antiferromagnetic and ferromagnetic materials holds a key role in today's magneto electronic devices. Models describing this phenomenon rely on the creation of a planar domain wall at the FM/AF interface when the ferromagnet magnetization is rotated. However, measurements of interface and antiferromagnetic properties have been a big challenge up to now. In this contest we have been able to confirm for the first time experimentally the presence of a such domain wall at the interface of Co/NiO systems by means of X-ray magnetic linear dichroism. Different Co/NiO samples have been studied as a function of the NiO structure (single crystal, thick film and polycrystalline), temperature and magnetic treatments. The existence or not of a planar domain wall is discussed.

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